

AMENDMENTS TO THE CLAIMS:

This listing of claims replaces all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1 to 9. (Cancelled)

10. (Currently Amended) ~~An integrated circuit, including~~ A dielectric film comprising a carbon doped oxide (CDO) ~~CDO~~ film having a modulus of about 20 GPa or greater.

11. (Currently Amended) The ~~integrated circuit~~ dielectric of claim 10, wherein the CDO film has a dielectric constant of about 2 to about 4.

12. (Currently Amended) The ~~integrated circuit~~ dielectric of claim 10, wherein the CDO film has a dielectric constant less than about 3.

13. (Currently Amended) The ~~integrated circuit~~ dielectric of claim 10, wherein the CDO film has a density less than about 2 g/cm<sup>3</sup>.

14. (Currently Amended) The ~~integrated circuit~~ dielectric of claim 10, wherein the CDO film has a density of about 1.3 g/cm<sup>3</sup> to about 1.4 g/cm<sup>3</sup>.

15. (Currently Amended) The ~~integrated circuit~~ dielectric of claim 11, wherein the dielectric comprises film is an interlevel dielectric film.

16. (Currently Amended) The ~~integrated circuit~~ dielectric of claim 10, wherein the CDO film has a modulus of about 20 GPa to about 25 GPa.

17. (Currently Amended) The ~~integrated circuit~~ dielectric of claim 16, wherein the dielectric has a dielectric constant is of about 2 to about 4.

18. (Currently Amended) The ~~integrated circuit~~ dielectric of claim 17, wherein the dielectric comprises film is an interlevel dielectric film.

19. (Currently Amended) ~~An integrated circuit, including~~ A dielectric film comprising a carbon doped oxide (CDO) ~~CDO~~ film having a hardness of about 2.8 GPa ~~or greater to about 3.5 GPa.~~

20. (Currently Amended) The ~~integrated circuit~~ dielectric of claim 19, wherein the CDO film has a dielectric constant of about 2 to about 4.

21. (Currently Amended) The ~~integrated circuit~~ dielectric of claim 20, wherein the dielectric comprises ~~film~~ is an interlevel dielectric film.

22. (Canceled)

23. (Currently Amended) The ~~integrated circuit~~ dielectric of claim ~~22~~ 19, wherein the CDO film has a dielectric constant of about 2 to about 4.

24. (Currently Amended) The ~~integrated circuit~~ dielectric of claim 23, wherein the dielectric ~~film~~ is comprises an interlevel dielectric film.

25. (Currently Amended) ~~An integrated circuit, including~~ A dielectric ~~film~~ comprising a carbon doped oxide (CDO) ~~CDO~~ film having a hardness of about 2.8 GPa or greater and a modulus of about 20 GPa or greater.

26. (Currently Amended) The ~~integrated circuit~~ dielectric of claim 25, wherein the CDO film has a hardness of about 2.8 GPa to about 3.5 GPa and a modulus of about 20 GPa to about 25 GPa.

27. (Currently Amended) The ~~integrated circuit~~ dielectric of claim 26, wherein the CDO film has a dielectric constant of about 2 to about 4.

Applicant : Lawrence D. Wong  
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28. (Currently Amended) The ~~integrated circuit~~ dielectric of claim 27, wherein the dielectric comprises ~~film~~ is an interlevel dielectric film.